

Final Product Change Notification

Issue Date:30-Apr-2014Effective Date:29-Jul-2014

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201404015F01



QUALITY

Change Category

[] Wafer Fab process	[] Assembly Process	[X] Product Marking
[]Wafer Fab	[] Assembly	[] Electrical spec./Test
materials	Materials	coverage
[X] Wafer Fab location	[] Assembly Location	[] Test Location

[] Design [] Mechanical Specification

[] Packing/Shipping/Labeling

PowerMOS - Addtional location for TrenchMOS Diffusion

Details of this Change

Products made using the T6 TrenchMOS silicon process sourced from Global Foundries, Singapore, have been qualified in to the NXP Manchester UK Fab

Why do we Implement this Change

Further to the introduction of dual source supply of T6 products from Singapore and Manchester, NXP is now extending this dual source capability to the remaining T6 designs in other packages. Dual sourcing provides our customers with enhanced supply chain flexibility and reliability.

Identification of Affected Products

Top side marking

Devices from Manchester will be identified by `E` Devices from Global Foundries, Singapore will be identified by `s`

Product Availability

Sample Information Samples are available upon request Production

Planned first shipment 07-Jul-2014

Impact

no impact to the product's functionality anticipated.

The constituent layers and the physical dimensions of finished devices will be identical.

The finished products will be electrically identical on all parameters, both static and dynamic

Data Sheet Revision

No impact to existing datasheet

Disposition of Old Products

The Manchester Fab will be introduced as an additional source, therefore products using wafers from both Singapore and Manchester will be shipped in parallel.

Related Notifications				
	Notification	Issue Date	Effective Date	Title
	201111031F01	09-Jul-2012	09-Aug-2012	PowerMOS - Additional location for TrenchMOS diffusion
	201303013F01	31-Mar-2013	29-Jun-2013	PowerMOS - Additional location for TrenchMOS diffusion
	201306008F01	17-Jul-2013	15-Oct-2013	PowerMOS - Addtional location for TrenchMOS Diffusion
	201312012F01	20-Dec-2013	20-Mar-2014	PowerMOS - Addtional location for TrenchMOS Diffusion
	201404010F01	28-Apr-2014	27-Jul-2014	PowerMOS - Addtional location for TrenchMOS Diffusion

Timing and Logistics

Your acknowledgement of this change, conform JEDEC JESD46 D, is expected till 30-May-2014.

Contact and Support

For all inquiries regarding the ePCN tool application or access issues, please <u>contact NXP "Global Quality</u> <u>Support Team"</u>.

For all Quality Notification content inquiries, please contact your local NXP Sales Support team.

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NXP Quality Management Team.

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